

1320um×711um Silicon PSD Chip datasheet

P/N : WS9N-01A

Application

Si PIN photodiode chips

Structure

Planar type : PIN diode

Electrodes :

Top side (Cathode) : Al

Backside (Anode) : Au Alloy

DIMENSIONS

Conditions	Min.	Typ.	Max.	Unit
Active	23 × 22 × 2 (±0.5)			mil
Chip width	52 × 28 (±0.5)			mil
Chip length	52 × 28 (±0.5)			mil
Chip height	12 (± 1.0)			mil
Pad N(Cathode)	2.4 (±0.2)			mil
Pad P(Anode)	2.4 (±0.2)			mil

Electro-Optical Characteristics (@ Ta = 25 °C)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward Voltage	VF	IF=10mA, H=0	0.5	0.72	1.3	V
Reverse Voltage	VBR	IR=100μA, H=0	35			V
Reverse Dark Current	ID	VR=10V, H=0			10	nA
Sensitive Wavelength Range	λp			940		nm
Capacitance	CJ	VR=5V, F=1 MHz		10		pF

